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01/07/02

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10042060	FILING DATE 01/07/2002	CLASS 117	SUBCLASS	GAU 1765	EXAMINER ANDERSON
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**APPLICANTS: Kuhn Harald; Stein Rene; Voelkl Johannes;

**CONTINUING DATA VERIFIED:

THIS APPLICATION IS A CON OF PCT/DE00/02174 07/04/2000

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** FOREIGN APPLICATIONS VERIFIED:

GERMANY 199 31 333.4 07/07/1999

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met Verified and Acknowledged Examiners's initials		yes <input checked="" type="checkbox"/> no yes <input checked="" type="checkbox"/> no	ATTORNEY DOCKET NO GR99P3456
TITLE : Method for the sublimation growth of an SiC single crystal, involving heating under growth pressure			

U.S. DEPT. OF COMM./PAT & TM-PTO-436L(Rev. 12-94)

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NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Assistant Examiner	
ISSUE FEE		Total Claims Print Claim for O.G	
Amount Due	Date Paid	DRAWING	
		Sheets Drwg. Figs.Drwg. Print Fig.	
TERMINAL DISCLAIMER		Primary Examiner	
		Application Examiner	
PREPARED FOR ISSUE			
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